

METHOD OF FORMING REFRACTORY METAL CONTACT IN AN OPENING, AND RESULTING STRUCTURE

Abstract

A structure which ensures against deterioration of an underlying silicide layer over which a refractory material layer is deposited by physical vapor deposition (PVD) or chemical vapor deposition (CVD) is realized by first providing a continuous polysilicon layer prior to the refractory material deposition. The continuous polysilicon layer, preferably no thicker than 50 Å, serves a sacrificial purpose and prevents damage to an underlying silicide layer by blocking interaction between any fluorine and the underlying silicide that is released when the refractory material is formed.